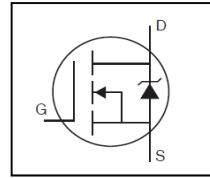


- Surface Mount
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

HEXFET® Power MOSFET



V_{DSS}	55V
R_{DS(on)}	0.045Ω
I_D	3.7A



SOT-223

G	D	S
Gate	Drain	Source

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SOT-223 package is designed for surface-mount using vapor phase, infra red, or wave soldering techniques. Its unique package design allows for easy automatic pick-and-place as with other SOT or SOIC packages but has the added advantage of improved thermal performance due to an enlarged tab for heat sinking. Power dissipation of 1.0W is possible in a typical surface mount application.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFL4105PbF	SOT-223	Tape and Reel	2500	IRFL4105PbF

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V ⑥	5.2	A
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V ⑤	3.7	
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V ⑤	3.0	
I _{DM}	Pulsed Drain Current ①	30	
P _D @ T _A = 25°C	Maximum Power Dissipation (PCB Mount) ⑥	2.1	W
P _D @ T _A = 25°C	Maximum Power Dissipation (PCB Mount) ⑤	1.0	
	Linear Derating Factor (PCB Mount) ⑤	8.3	mW/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	110	mJ
I _{AR}	Avalanche Current ①	3.7	A
E _{AR}	Repetitive Avalanche Energy ①	0.10	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		

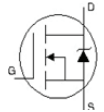
Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJA}	Junction-to-Ambient (PCB Mount, steady state) ⑤	90	120	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mount, steady state) ⑥	50	60	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

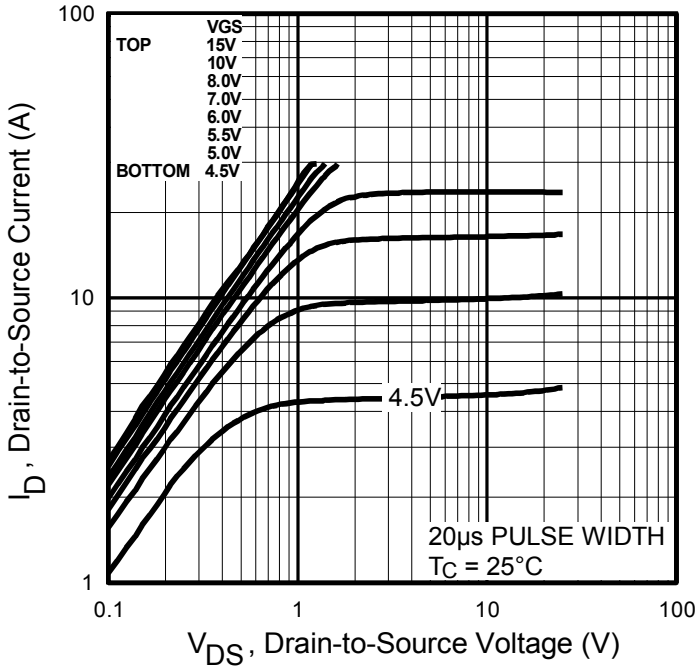
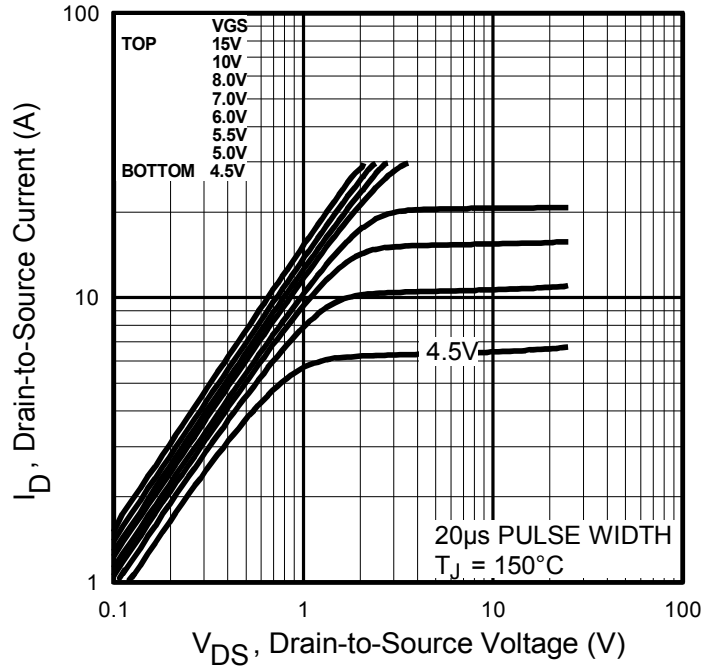
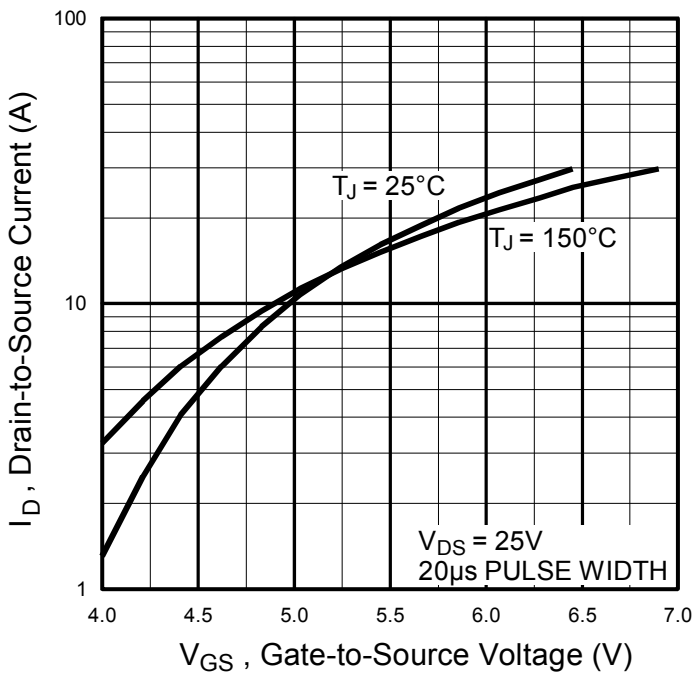
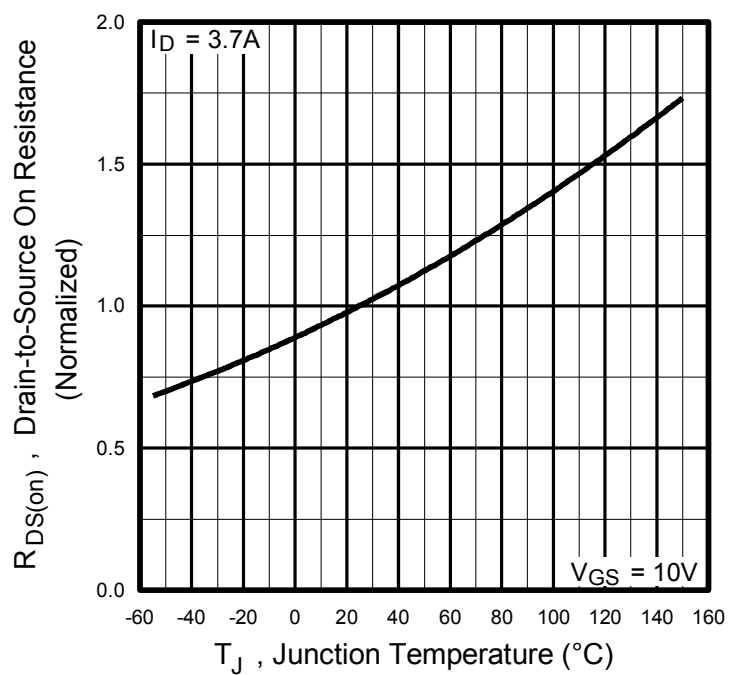
	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.058	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.045	Ω	V _{GS} = 10V, I _D = 3.7A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Trans conductance	3.8	—	—	S	V _{DS} = 25V, I _D = 1.9A
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 55 V, V _{GS} = 0V
		—	—	250		V _{DS} = 44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	23	35	nC	I _D = 3.7A
Q _{gs}	Gate-to-Source Charge	—	3.4	5.1		V _{DS} = 44V
Q _{gd}	Gate-to-Drain Charge	—	9.8	15		V _{GS} = 10V, See Fig. 6 and 13 ④
t _{d(on)}	Turn-On Delay Time	—	7.1	—	ns	V _{DD} = 28V
t _r	Rise Time	—	12	—		I _D = 3.7A
t _{d(off)}	Turn-Off Delay Time	—	19	—		R _G = 6.0Ω
t _f	Fall Time	—	12	—		R _D = 7.5Ω, See Fig. 10 ④
C _{iss}	Input Capacitance	—	660	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	230	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	99	—		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	30		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 3.7A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	55	82	ns	T _J = 25°C, I _F = 3.7A
Q _{rr}	Reverse Recovery Charge	—	120	170	nC	di/dt = 100A/μs ④

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② starting T_J = 25°C, L = 16mH, R_G = 25Ω, I_{AS} = 3.7A (See fig. 12)
- ③ I_{SD} ≤ 3.7A, di/dt ≤ 110A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Normalized On-Resistance vs. Temperature

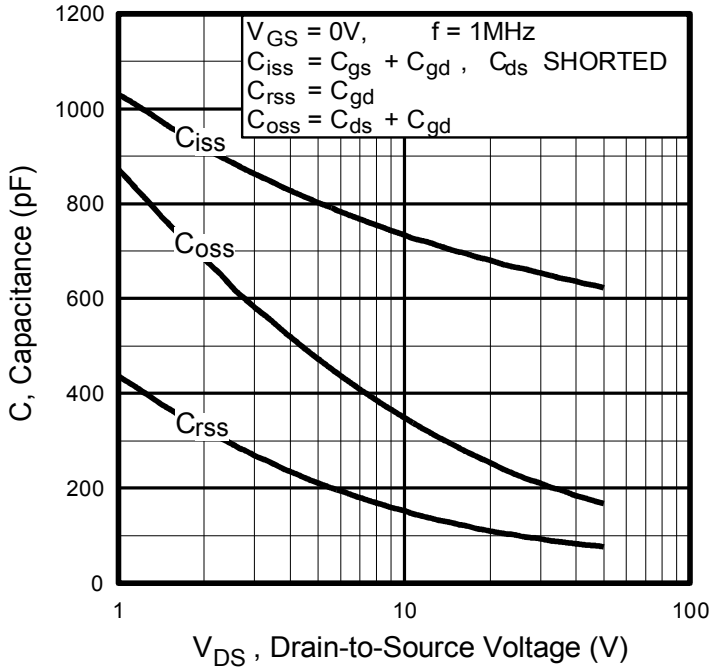


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

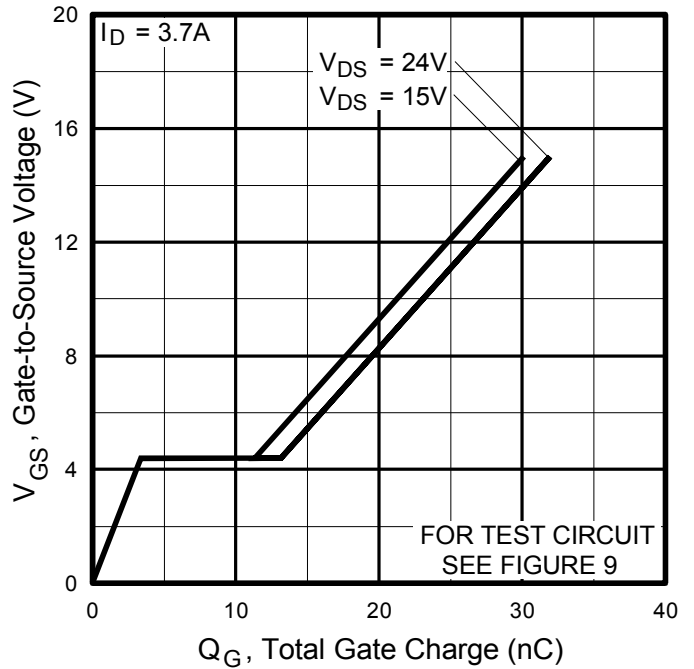


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

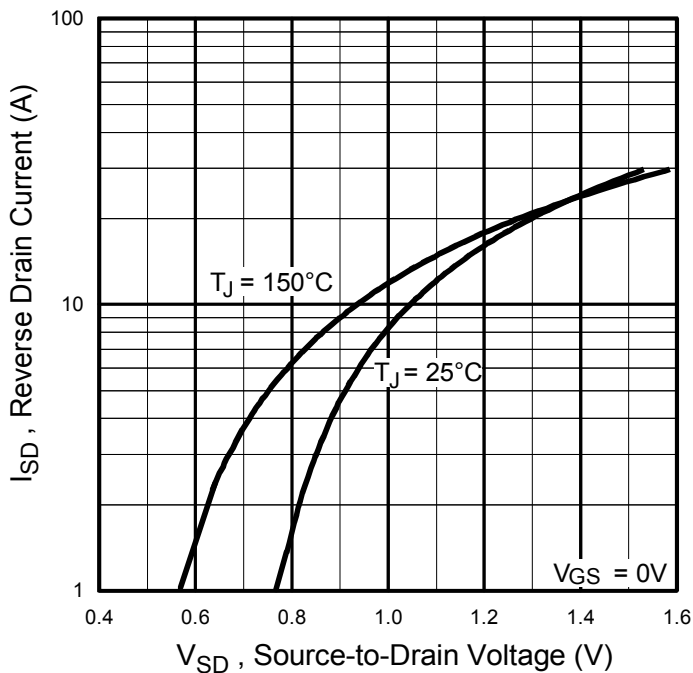


Fig 7 Typical Source-to-Drain Diode Forward Voltage

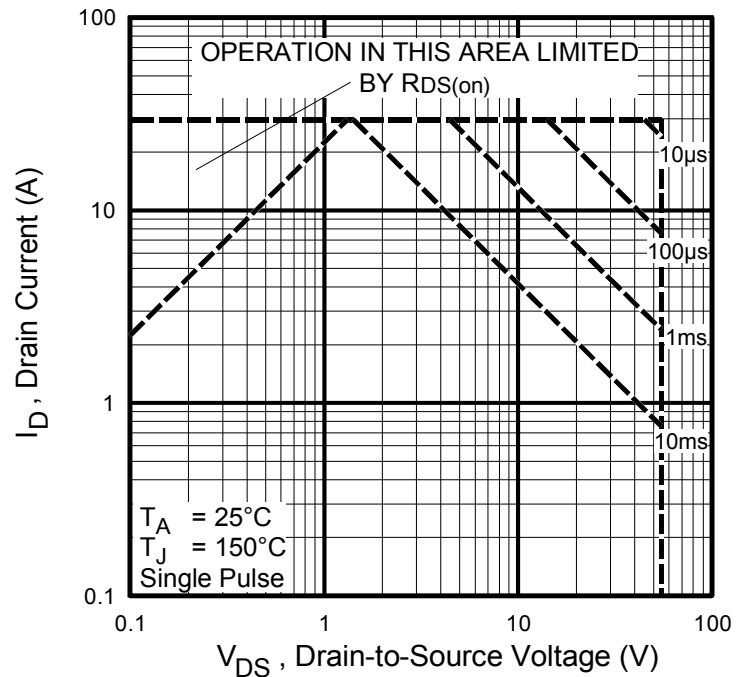
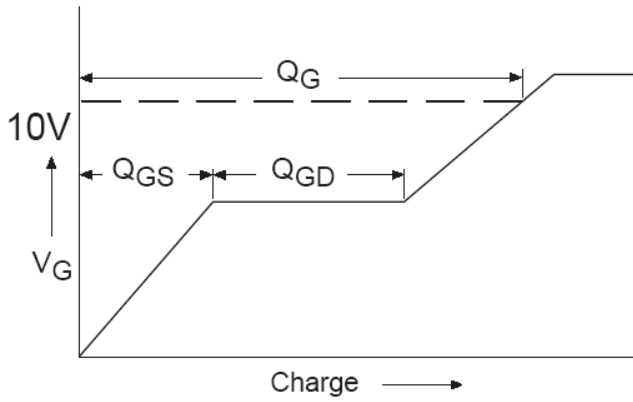
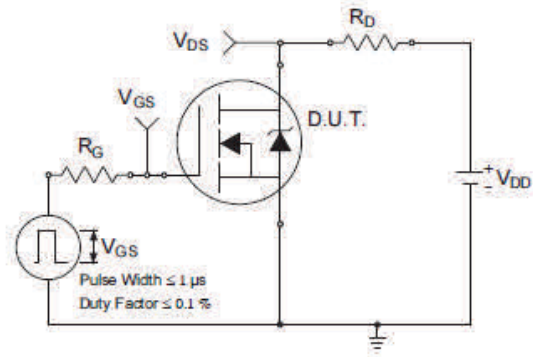
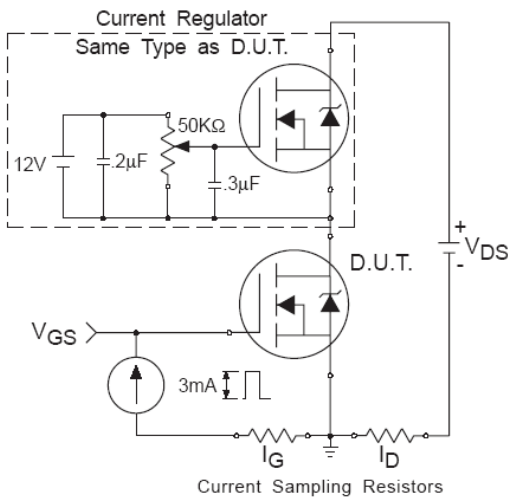
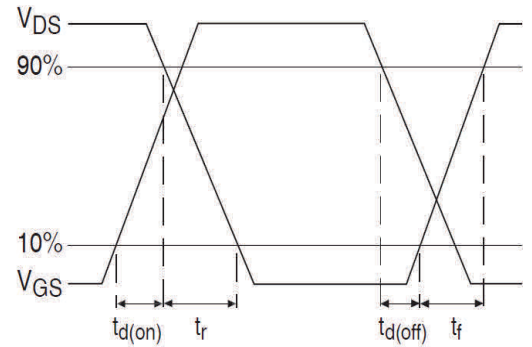
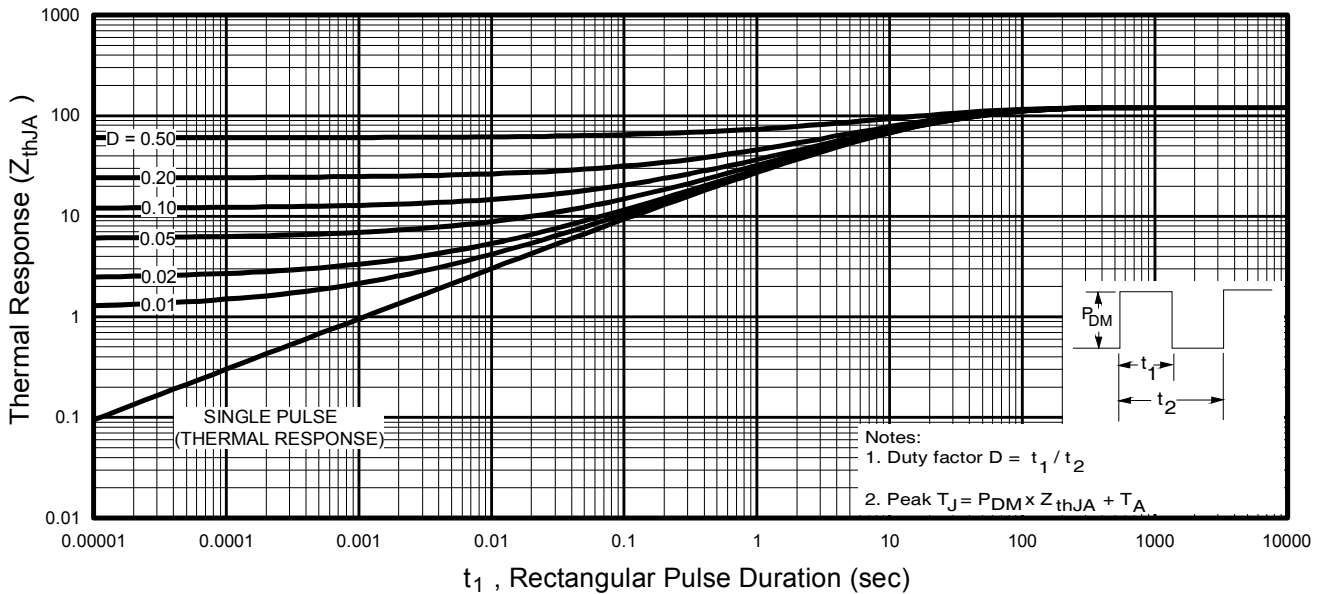


Fig 8. Maximum Safe Operating Area


Fig 9a. Basic Gate Charge Waveform

Fig 10a. Switching Time Test Circuit

Fig 9b. Gate Charge Test Circuit

Fig 10b. Switching Time Waveforms

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

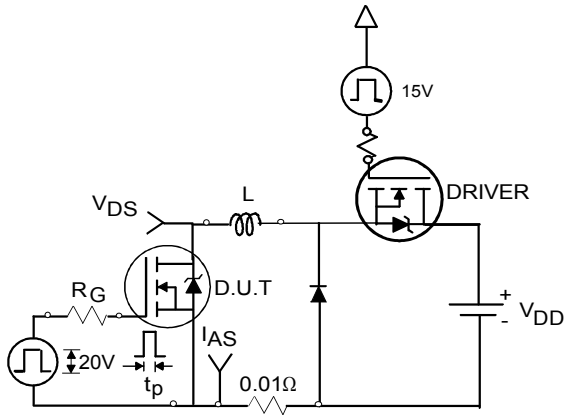
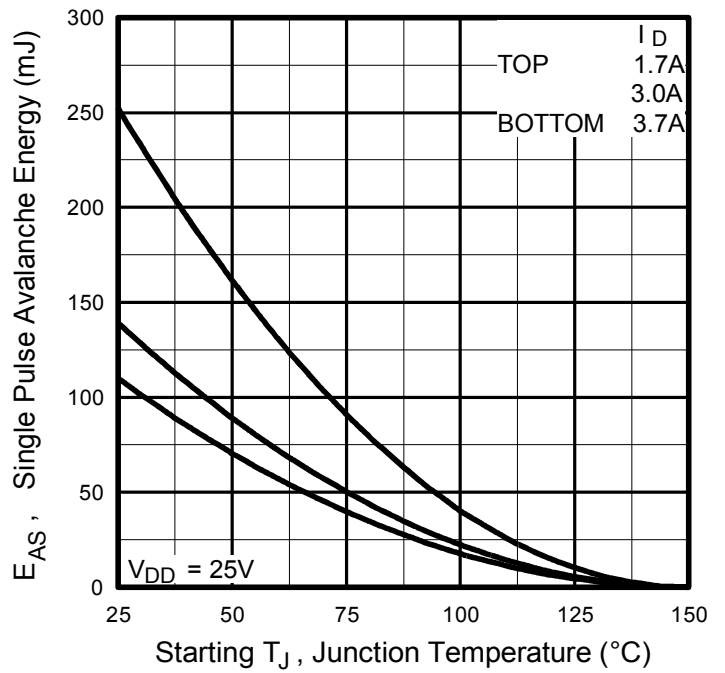
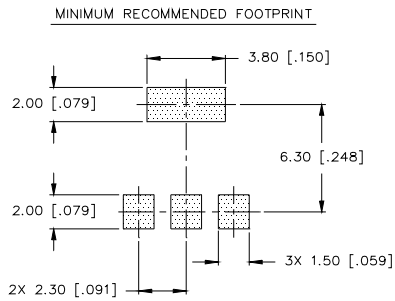
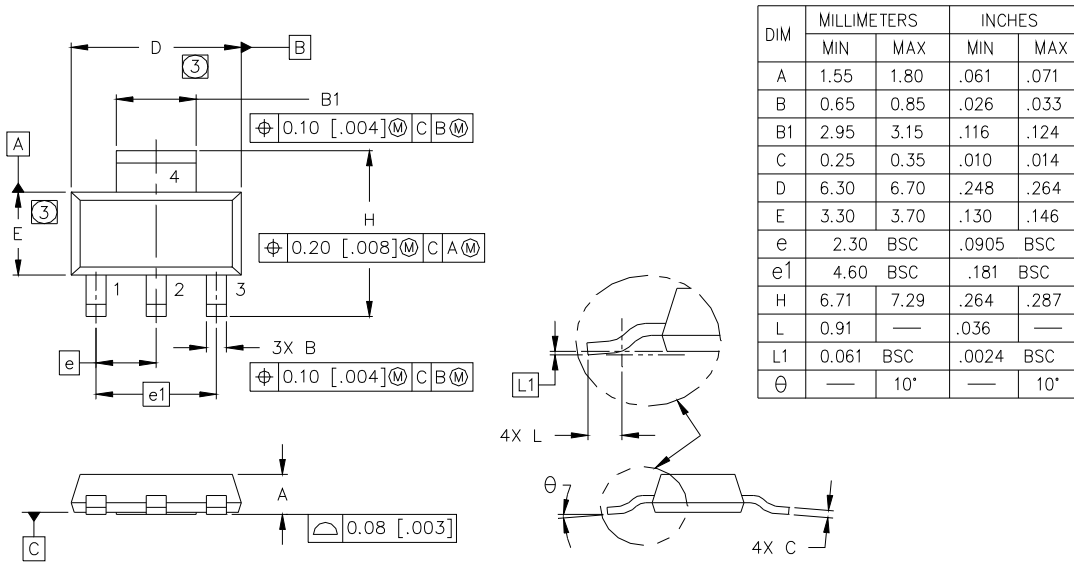

Fig 12a. Unclamped Inductive Test Circuit

Fig 12c. Maximum Avalanche Energy vs. Drain Current

Fig 12b. Unclamped Inductive Waveforms

Peak Diode Recovery dv/dt Test Circuit



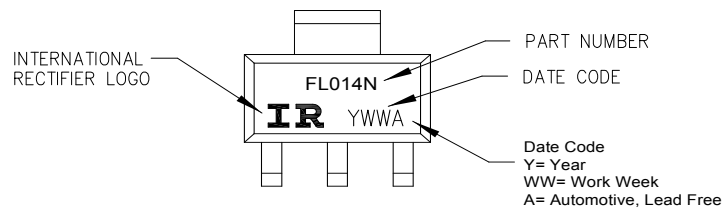
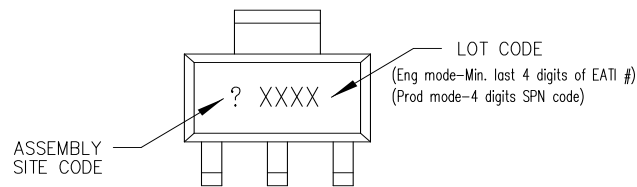
Fig 13. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

SOT-223 (TO-261AA) Package Outline (Dimensions are shown in millimeters (inches))

LEAD ASSIGNMENTS

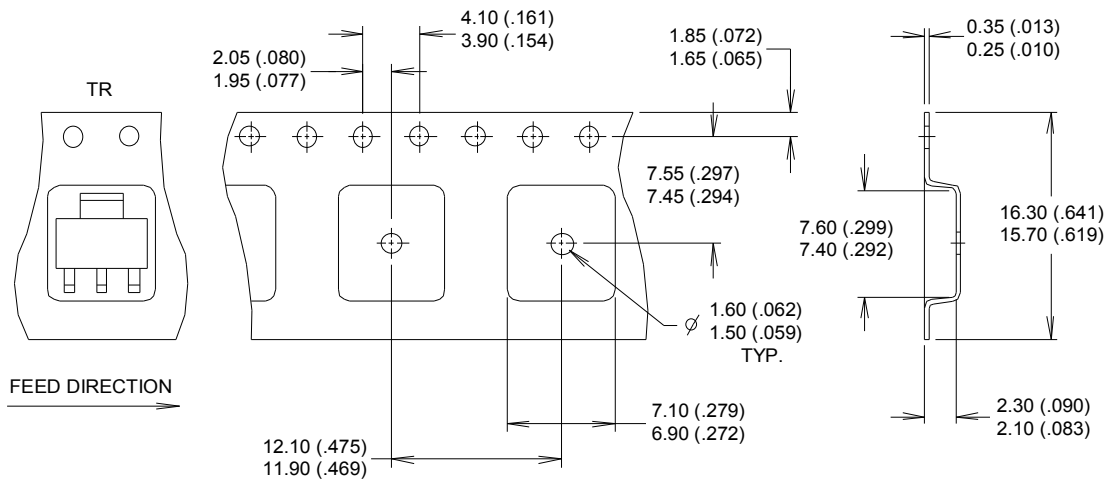
- 1 = GATE
- 2 = DRAIN
- 3 = SOURCE
- 4 = DRAIN

NOTES:

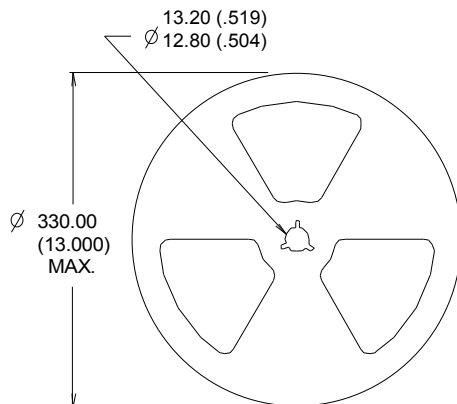
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
- ③ DIMENSIONS DO NOT INCLUDE MOLD FLASH.
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
5. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

SOT-223(TO-261AA) Part Marking Information

TOP MARKING

BOTTOM MARKING

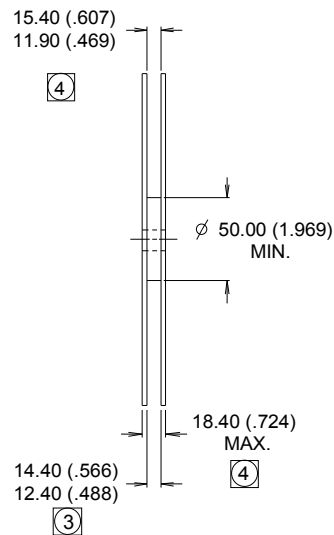
Note: For the most current drawing please refer to Infineon's web site www.infineon.com

SOT-223(TO-261AA) Tape and Reel (Dimensions are shown in millimeters (inches))

NOTES :

1. CONTROLLING DIMENSION: MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.
3. EACH $\varnothing 330.00$ (13.00) REEL CONTAINS 2,500 DEVICES.


NOTES :

1. OUTLINE CONFORMS TO EIA-418-1.
2. CONTROLLING DIMENSION: MILLIMETER..
- ③ DIMENSION MEASURED @ HUB.
- ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.



Note: For the most current drawing please refer to Infineon's web site www.infineon.com

Qualification Information[†]

Qualification Level	Industrial (per JEDEC JESD47F) ^{††}	
Moisture Sensitivity Level	SOT-223	MSL1 (per JEDEC J-STD-020D) ^{††}
RoHS Compliant	Yes	

† Qualification standards can be found at Infineon's web site www.infineon.com

†† Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comments
5/27/2016	<ul style="list-style-type: none"> Updated datasheet with corporate template. Added disclaimer on last page.

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Edition 2016-04-19

Published by

Infineon Technologies AG

81726 Munich, Germany

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